

**SUBSTRATE COMPRISING A THICK BURIED DIELECTRIC LAYER AND
METHOD FOR PREPARING SUCH A SUBSTRATE**

Abstract

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The invention relates to a final substrate (S) comprising, consecutively and in contact with one another, an upper layer (5) made of semiconductor material, a dielectric layer (4) having a thickness greater than 200 nm, an electrical charge
10 trapping layer (2) and a base substrate (3). The final substrate (S) has a curvature of less than 60 micrometres, preferably less than 40 micrometres. An exposed surface of the upper layer (5) has a roughness of less than 0.3 nm as a root mean square measurement over a field of 30 micrometres
15 by 30 micrometres. The invention also relates to a method for preparing such a substrate.

Fig. 3